



# Bipolar PNP Bare Die – BTP121

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## Part Description

The BTP121 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN121

## Key Parameters:

- VCBO = -40V
- VCEO = -32V
- VEBO = -5V
- hFE = 82-390 @ VCE = -3V, IC = -0.01A
- VCE(Sat) = -0.4V @ IC = -0.1A, IB = -10mA
- fT = 200 MHz @ VCE = -5V, IE = 0A
- COBO = 8pF @ VCB = -10V

## Features

Low VCE(sat)

## Die Size (Unawn)

560µm X 560µm, 22 Mils X 22 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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